New Family of GaN on SiC HEMT RF Transistors

Richardson RFPD announces immediate availability and full design support capabilities for a new family of gallium nitride (GaN) on silicon carbide (SiC), high electron mobility transistor (HEMT), radio frequency (RF) transistors from Microsemi Corporation (Microsemi).

The common source GaN on SiC transistors are internally-matched for optimal performance and specifically designed for S-band radar applications, making them easier to design-in than unmatched broadband devices. Peak output power levels range from 110-280W (Class AB), with high power gain and drain efficiency across the frequency band and under pulse conditions specified with a power supply of 60V. The devices utilize gold metallization and eutectic attach to provide the highest reliability and superior ruggedness.

Key features of the new family of devices include:

Part Number	**Frequency** (GHz)	**Pout** (W)	**Gain** (dB)	**PW** (µs)	**DF** %
2729GN-150	2.7-2.9	150	13	100	10
2729GN-270	2.7-2.9	280	14	100	10

2731GN-110	2.7-3.1	110	12	200	10
2731GN-200	2.7-3.1	200	12	200	10
3135GN-170	3.1-3.5	170	11	300	10

The devices are in stock and available for immediate delivery. To find more information, or to purchase these products today on the Richardson RFPD website, please visit the Microsemi GaN on SiC HEMT RF Transistors webpage. The devices are also available by calling 1-800-737-6937 (within North America); or please find your local sales engineer (worldwide) at Local Sales Support. To learn more about additional products from Microsemi, please visit the Microsemi storefront webpage.

More information is available online at www.richardsonrfpd.com [1].

Posted by Janine E. Mooney, Editor

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[1] http://www.richardsonrfpd.com